

Abstract of Disclosure

Provided with a semiconductor device including: a semiconductor substrate having a first conductivity type; a first well having a second conductivity type formed in a first 5 region in a major surface of the semiconductor substrate; a second well having the first conductivity type formed in a second region in the major surface of the semiconductor substrate; a first MOS transistor having the first conductivity type and a first contact region having the second conductivity type formed in the first well; a second MOS 10 transistor having the second conductivity type and a second contact region having the second conductivity type formed in the second well; a heavily doped region of buried layer having the second conductivity type formed at a portion corresponding 15 to the first contact region in the first well; and a heavily doped region of buried layer having the first conductivity type formed at a portion corresponding to the second contact region in the second well.